

Silicon PNP Power Transistors

2SA1185

DESCRIPTION

- With TO-3PN package
- High current capability
- Low collector saturation voltage

APPLICATIONS

- High power amplifier applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

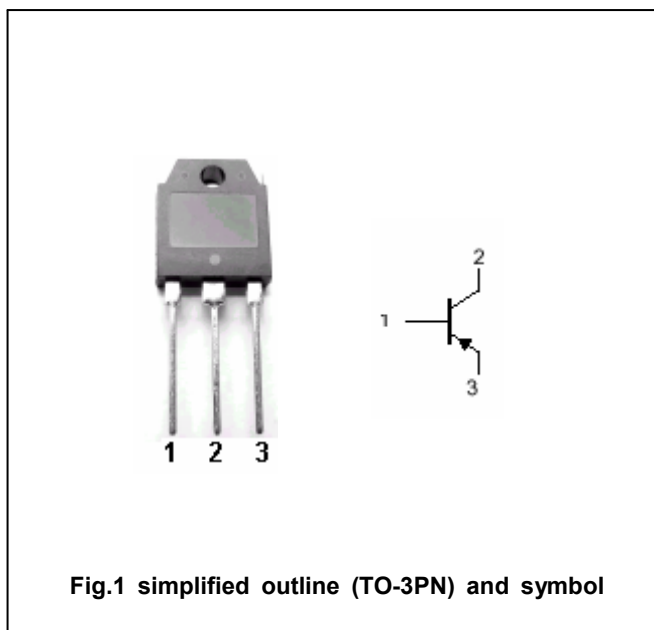


Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-50	V
V _{CEO}	Collector-emitter voltage	Open base	-50	V
V _{EBO}	Emitter-base voltage	Open collector	-5	V
I _C	Collector current		-7	A
I _{CM}	Collector current-peak		-15	A
I _{BM}	Base current-peak		-5	A
P _C	Collector power dissipation	T _C =25□	60	W
T _j	Junction temperature		150	□
T _{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-0.1A ; I _B =0	-50			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-7A; I _B =-0.7A			-0.8	V
V _{BE}	Base-emitter on voltage	I _C =-7A ; V _{CE} =-5V			-1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =-50V; I _E =0			-1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-2	mA
h _{FE-1}	DC current gain	I _C =-1A ; V _{CE} =-5V	60		320	
h _{FE-2}	DC current gain	I _C =-7A ; V _{CE} =-5V	20			
C _{ob}	Output capacitance	I _E =0 ; V _{CB} =-10V; f=1MHz		250		pF
f _T	Transition frequency	I _C =-0.5A ; V _{CE} =-5V		100		MHz

◆ h_{FE-1} Classifications

Q	P	O
60-120	100-200	160-320

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PACKAGE OUTLINE

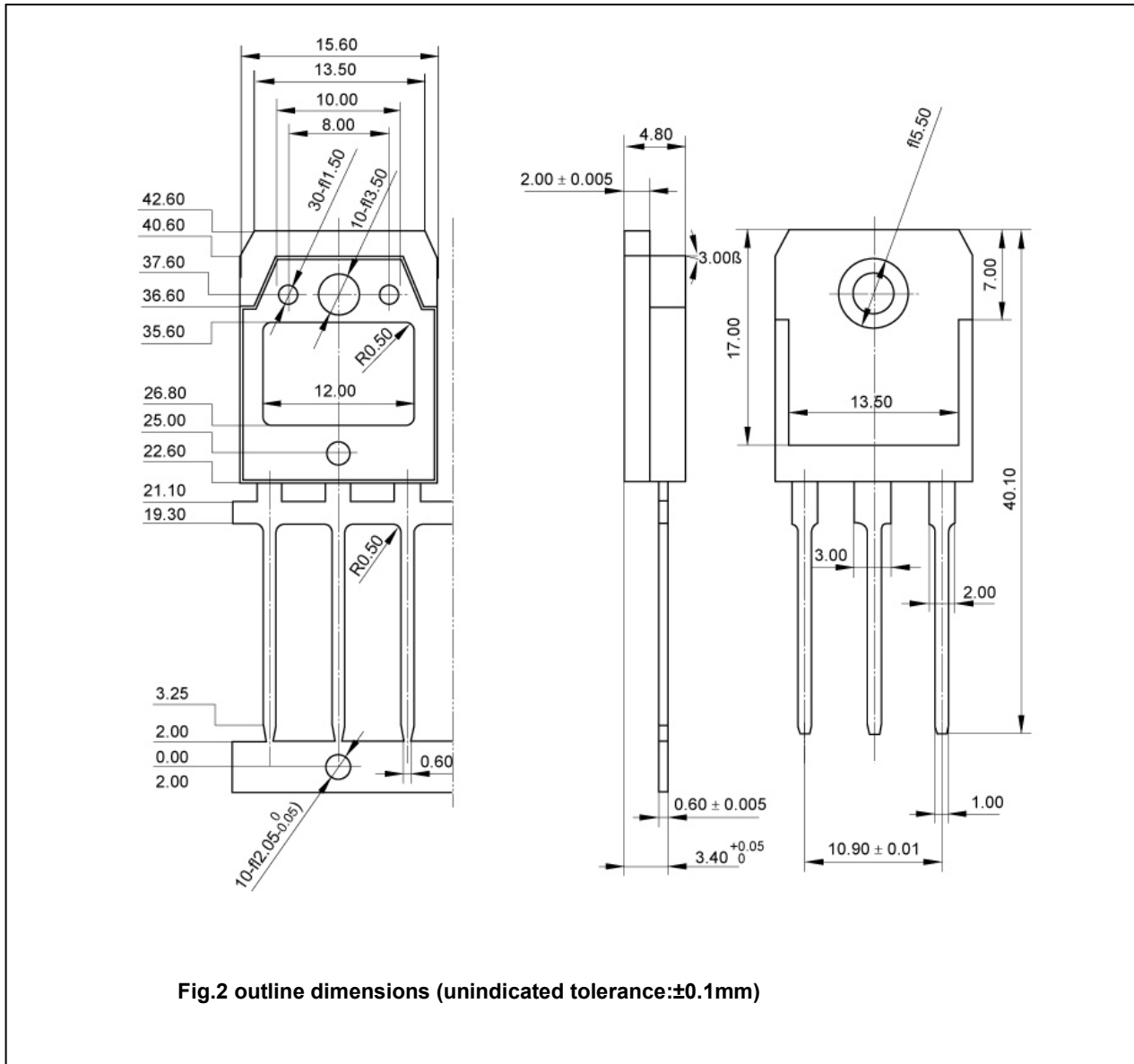


Fig.2 outline dimensions (unindicated tolerance:±0.1mm)